















**ESD** 

TVS

MOS

LDO

Diode

Sensor

DC-DC

# **Product Specification**

Domestic Part Number	IRFP4468
Overseas Part Number	IRFP4468
▶ Equivalent Part Number	IRFP4468





### **Thunder High Power Products**

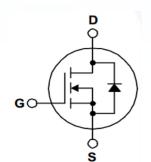
### Silicon N-Channel Power MOSFET

#### • FEATURES

- Static drain-source on-resistance: R<sub>DS</sub>(on)≤2.6mΩ
- Enhancement mode: Vth =2.0 to 4.0 V (VDS=VGS, ID=250 μ A)
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

#### DESCRITION

- High Efficiency Synchronous Rectification in SMPS
- Uninterruptible Power Supply
- High Speed Power Switching
- · Hard Switched And High Frequency Circuits



### • ABSOLUTE MAXIMUM RATINGS(T<sub>a</sub>=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>DSS</sub>	Drain-Source Voltage	100	V
V <sub>GS</sub>	Gate-Source Voltage	±20	V
I <sub>D</sub>	Drain Current-Continuous	195	Α
I <sub>DM</sub>	Drain Current-Single Pulsed	1120	А
P <sub>D</sub>	Total Dissipation @T <sub>C</sub> =25℃	520	W
Tj	Max. Operating Junction Temperature	175	°C
T <sub>stg</sub>	Storage Temperature	-55~175	°C

#### • THERMAL CHARACTERISTICS

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SYMBOL	PARAMETER	MAX	UNIT
Rth(j-c)	Channel-to-case thermal resistance	0.29	°C/W
Rth(j-a)	Channel-to-ambient thermal resistance	40	°C/W



### Thunder High Power Products

### **Silicon N-Channel Power MOSFET**

### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

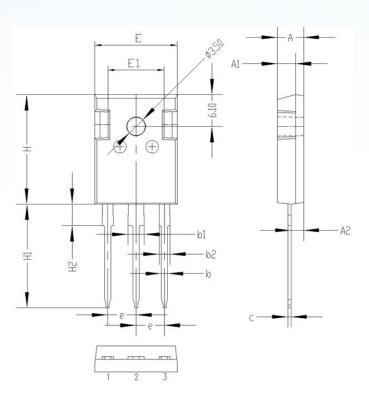
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SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V; I <sub>D</sub> =250 μ A	100			V
V <sub>GS(th)</sub>	Gate Threshold Voltage	VDS=VGS; I <sub>D</sub> =250 μ A	2.0		4.0	V
$R_{DS(on)}$	Drain-Source On-Resistance	V <sub>GS</sub> =10V; I <sub>D</sub> =180A			2.6	mΩ
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> = ±20V			±0.1	μА
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =100V; V <sub>GS</sub> = 0V			20	μА
V <sub>SD</sub>	Diode forward voltage	I <sub>S</sub> =180A, V <sub>GS</sub> = 0V			1.3	V



# Thunder High Power Products

### **Package Information**





Cumbal	Dimensions(millimeters)		
Symbol	Min.	Max.	
Α	4.80	5.20	
A1	3.30	3.70	
A2	2.10	2.50	
b	1.00	1.40	
b1	2.90	3.30	
b2	1.90	2.30	
С	0.40	0.80	
е	5.25	5.65	
Е	15.6	16.0	
E1	10.6	11.00	
Н	20.8	21.2	
H1	19.4	20.4	
H2	3.90	4.30	
G	5.90	6.30	
ΦР	3.30	3.70	



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